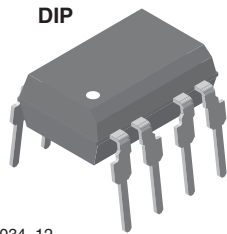
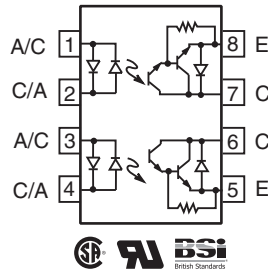


Optocoupler, Photodarlington Output, AC Input, Internal R_{BE}



i179034_12



FEATURES

- Internal R_{BE} for better stability
- BV_{CEO} > 60 V
- AC or polarity insensitive inputs
- Built-in reverse polarity input protection
- Industry standard DIP package
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC


RoHS
COMPLIANT

APPLICATIONS

- Designed for applications requiring detection or monitoring of AC signals

AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J, double protection
- CSA 93751
- BSI IEC 60950; IEC 60065

DESCRIPTION

The ILD766 are bidirectional input optically coupled isolators. They consist of two gallium arsenide infrared emitting diodes coupled to a silicon NPN photodarlington per channel.

The ILD766 has two isolated channels in a single DIP package.

| ORDERING INFORMATION | | | |
|---|----------|----------|--|
| <div style="display: flex; justify-content: space-around; align-items: center;"> <div style="border: 1px solid black; padding: 2px 5px;">I</div> <div style="border: 1px solid black; padding: 2px 5px;">L</div> <div style="border: 1px solid black; padding: 2px 5px;">D</div> <div style="border: 1px solid black; padding: 2px 5px;">7</div> <div style="border: 1px solid black; padding: 2px 5px;">6</div> <div style="border: 1px solid black; padding: 2px 5px;">6</div> <div style="margin: 0 10px;">-</div> <div style="border: 1px solid black; padding: 2px 5px;">#</div> </div> <p style="text-align: center; margin-top: 5px;">PART NUMBER CTR BIN</p> | | | |
| AGENCY CERTIFIED/PACKAGE | CTR (%) | | |
| | 2 mA | 1 mA | |
| UL, CSA, BSI | ≥ 500 | ≥ 500 | |
| DIP-8 | ILD766-1 | ILD766-2 | |

Note

- Additional options may be possible, please contact sales office.

| ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified) | | | | |
|---|----------------|-------------------|-------|-------|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
| INPUT | | | | |
| Forward current | | I _F | 60 | mA |
| Power dissipation | | P _{diss} | 90 | mW |
| Derate linearly | from 25 °C | | 1.2 | mW/°C |
| OUTPUT | | | | |
| Collector emitter breakdown voltage | | BV _{CEO} | 60 | V |
| Collector base breakdown voltage | | BV _{CBO} | 70 | V |
| Power dissipation | | P _{diss} | 100 | mW |
| Derate linearly | from 25 °C | | 1.33 | mW/°C |



| ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified) | | | | |
|---|---|-----------|----------------|-----------|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
| COUPLER | | | | |
| Total dissipation | | P_{tot} | 400 | mW |
| Derate linearly | from 25 °C | | 5.3 | mW/°C |
| Isolation test voltage | t = 1 s | V_{ISO} | 5300 | V_{RMS} |
| Isolation resistance | $T_{amb} = 25\text{ }^{\circ}\text{C}$ | R_{IO} | $\geq 10^{12}$ | Ω |
| | $T_{amb} = 100\text{ }^{\circ}\text{C}$ | R_{IO} | $\geq 10^{11}$ | Ω |
| Creepage distance | | | ≥ 7.0 | mm |
| Clearance distance | | | ≥ 7.0 | mm |
| Comparative tracking index per DIN IEC 112/VDE 0303, part 1 | | CTI | 175 | |
| Storage temperature | | T_{stg} | - 55 to + 150 | °C |
| Operating temperature | | T_{amb} | - 55 to + 100 | °C |
| Lead soldering time | at 260 °C | | 10 | s |

Note

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

| ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified) | | | | | | |
|---|--|-------------|------|------|------|------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| INPUT | | | | | | |
| Forward voltage | $I_F = \pm 10\text{ mA}$ | V_F | | 1.2 | 1.5 | V |
| OUTPUT | | | | | | |
| Collector emitter breakdown voltage | $I_C = 1.0\text{ mA}$ | BV_{CEO} | 60 | 75 | | V |
| Collector base breakdown voltage | $I_C = 10\text{ }\mu\text{A}$ | BV_{CBO} | 60 | 90 | | V |
| Collector emitter leakage current | $V_{CE} = 10\text{ V}$ | I_{CEO} | | 10 | 100 | nA |
| COUPLER | | | | | | |
| Collector emitter saturation voltage | $I_F = \pm 10\text{ mA}, I_C = 10\text{ mA}$ | V_{CEsat} | | | 1.0 | V |

Note

- Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

| CURRENT TRANSFER RATIO ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified) | | | | | | |
|---|--|------------|------|------|------|------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| DC current transfer ratio | $V_{CE} = 5.0\text{ V}, I_F = \pm 2\text{ mA}$ | CTR_{DC} | 500 | | | % |

| SWITCHING CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified) | | | | | | |
|--|--|--------|------|------|------|---------------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Rise time | $V_{CC} = 10\text{ V}, I_F = \pm 2.0\text{ mA}, R_L = 100\text{ }\Omega$ | t_r | | 100 | | μs |
| Fall time | | t_f | | 100 | | |

TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

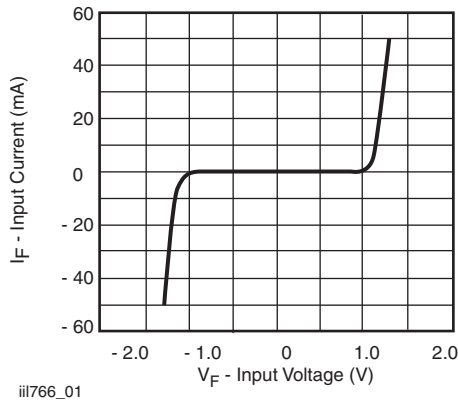


Fig. 1 - Input Characteristics

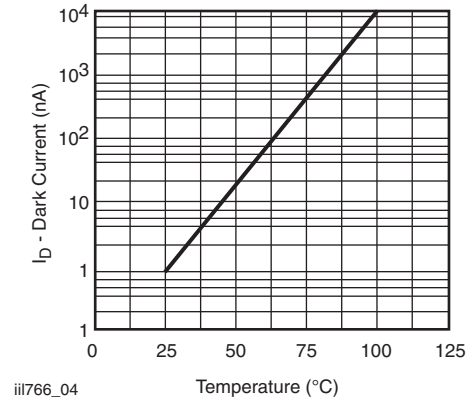


Fig. 4 - I_{CEO} at $V_{CE} = 10\text{ V}$ vs. Temperature

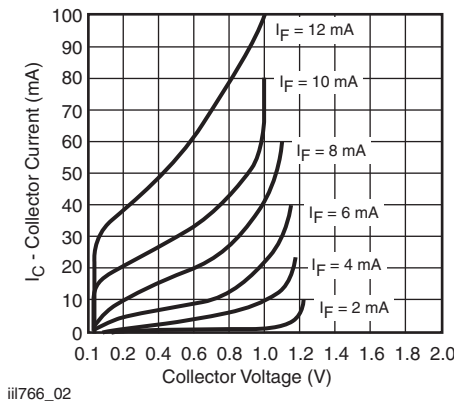


Fig. 2 - Transistor Current vs. Voltage

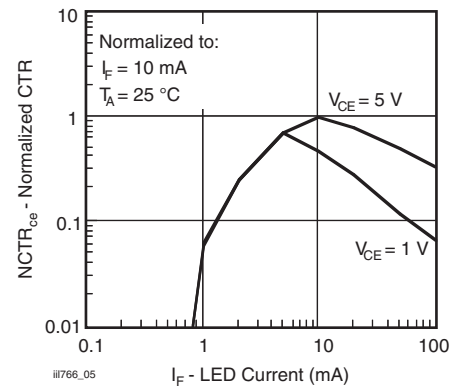


Fig. 5 - Normalized CTR vs. Forward Current

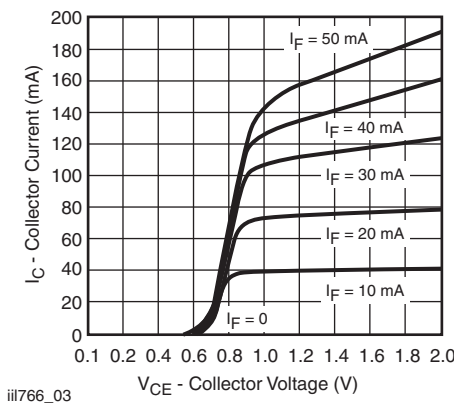


Fig. 3 - Transistor Output Current vs. Voltage

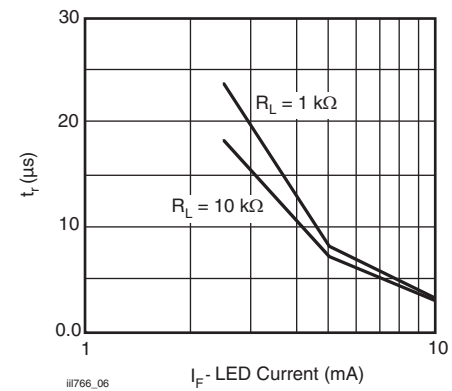
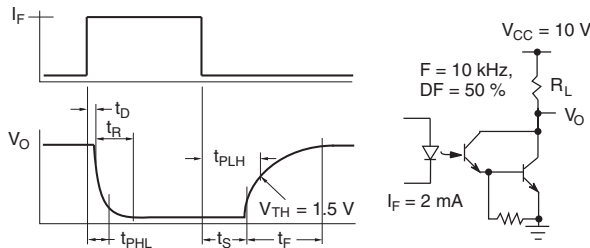
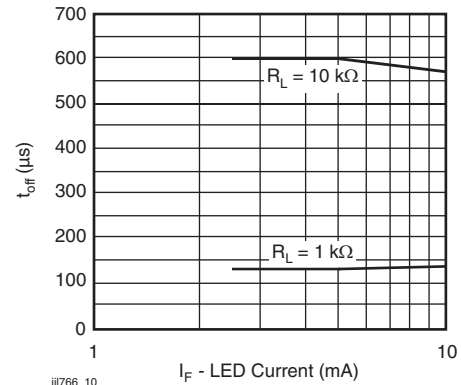


Fig. 6 - t_r vs. Forward Current



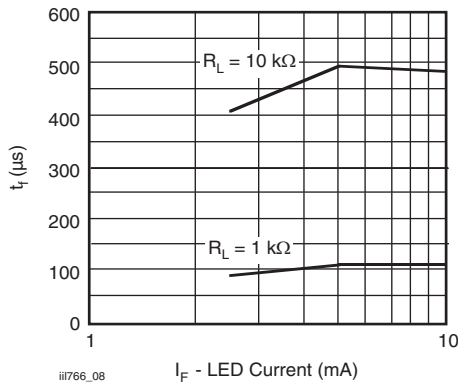
iii766_07

Fig. 7 - Saturated Switching Characteristics Measurements-Schematic and Waveform



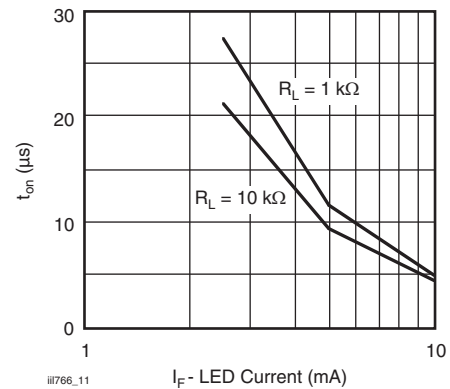
iii766_10

Fig. 10 - t_{off} vs. Forward Current



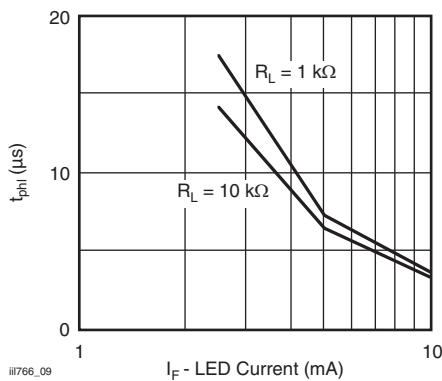
iii766_08

Fig. 8 - t_{fall} vs. Forward Current



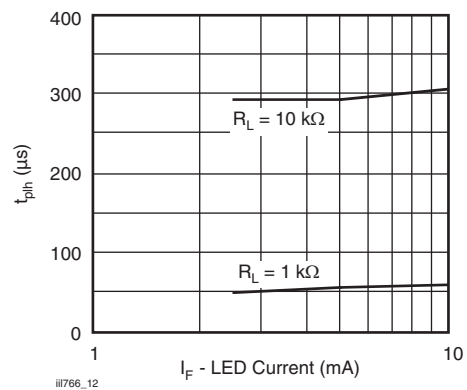
iii766_11

Fig. 11 - t_{on} vs. Forward Current



iii766_09

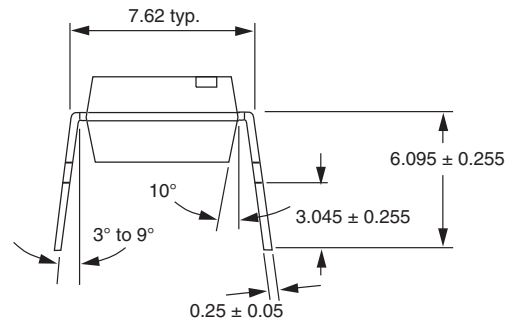
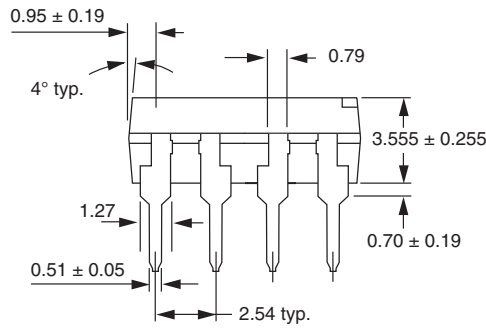
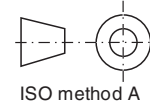
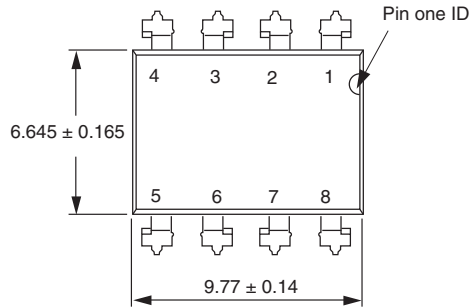
Fig. 9 - t_{phl} vs. Forward Current



iii766_12

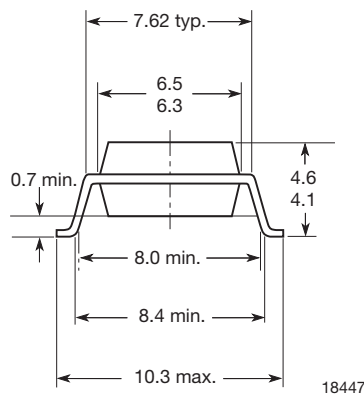
Fig. 12 - t_{plh} vs. Forward Current

PACKAGE DIMENSIONS in millimeters



i178006

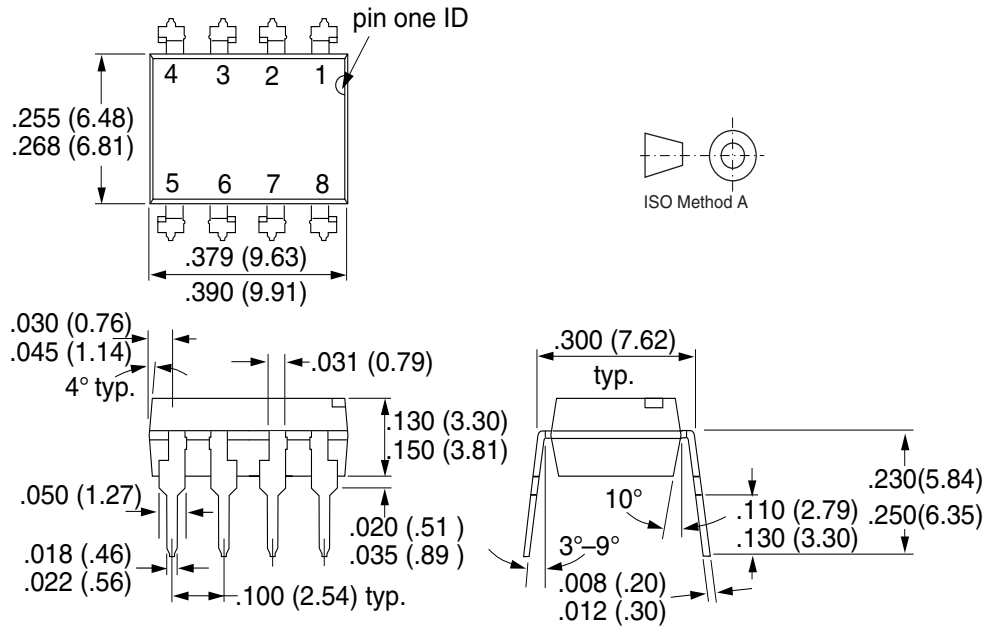
Option 7



18447

DIP-8

Package Dimensions in Inches (mm)



i178006

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2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

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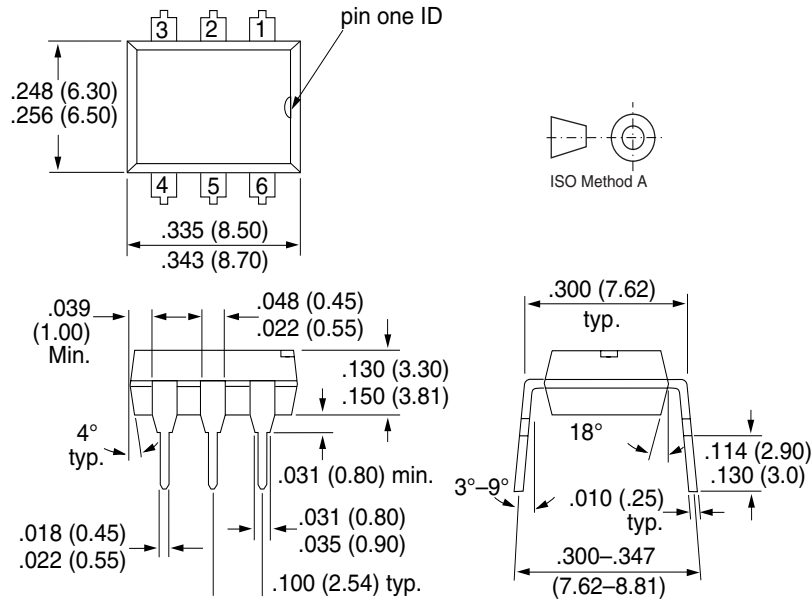
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Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany
Telephone: 49 (0)7131 67 2831, Fax number: 49 (0)7131 67 2423



DIP-6A

Package Dimensions in Inches (mm)



i178004

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